



# Bipolar NPN Bare Die – BTN6024

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## Part Description

The BTN6024 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. PNP Complement is BTP6025.

## Key Parameters:

- VCBO = 100V
- VCEO = 50V
- VEBO = 7V
- hFE = 400-1000 @ VCE = 2V, IC = 0.3A
- VCE(Sat) = 0.14V @ IC = 1A, IB = 20mA
- fT = 250 MHz @ VCE = 2V, IE = 0A
- COBO = 13pF @ VCB = 10V

## Features

Very Low VCE(sat). Designed to provide performance equivalent to TOSHIBA 2SC5714

## Die Size (Unawn)

790µm X 790µm, 31 Mils X 31 Mils

This is a shortform datasheet only

For the full datasheet

Please contact [sales@siliconsupplies.com](mailto:sales@siliconsupplies.com)

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